



60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C (Note 9)
60V	3.4mΩ @ V _{GS} = 10V	100A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_g Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMTH6004SCTBQ</u>)

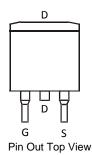
Mechanical Data

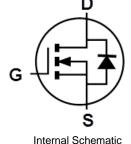
- Case: TO263AB
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 1.7 grams (Approximate)

TO263AB



Top View





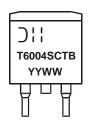
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH6004SCTB-13	TO263AB	800 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



T6004SCTB = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 15 = 2015) WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 6)	T _C = +25°C (Note 9)	I _D	100	А
,	T _C = +100°C	.5	100	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	100	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle=1%)	I _{DM}	200	Α	
Avalanche Current, L=0.2mH	I _{AS}	45	Α	
Avalanche Energy, L=0.2mH	E _{AS}	200	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_{D}	4.7	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	32	°C/W	
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	P_{D}	136	W
Thermal Resistance, Junction to Case (Note 6)		R _{eJC}	1.1	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	2	-	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		2.9	3.4	mΩ	$V_{GS} = 10V, I_{D} = 100A$	
Diode Forward Voltage	V_{SD}	_	_	1.3	V	$V_{GS} = 0V, I_S = 100A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	4,556	_		$V_{DS} = 30V$, $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	1	1,383	_	pF		
Reverse Transfer Capacitance	Crss		105.2	_			
Gate Resistance	R_g	_	0.66	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	95.4	_		V 00V I 00A	
Gate-Source Charge	Qgs	_	21.6	_	nC	$V_{DD} = 30V, I_D = 90A,$ $V_{GS} = 10V$	
Gate-Drain Charge	Q_{qd}	_	20.4	_			
Turn-On Delay Time	t _{D(ON)}	_	13.2	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 90A, R_{G} = 3.5\Omega$	
Turn-On Rise Time	t _R	_	11.7	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	31	_			
Turn-Off Fall Time	t _F		12	_			
Reverse Recovery Time	t _{RR}	_	50.5	_	ns	L 504 di/dt 4004/	
Reverse Recovery Charge	Q _{RR}	-	80.8	_	nC	-I _F =50A, di/dt=100A/μs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

^{6.} Thermal resistance from junction to soldering point (on the exposed drain pad).

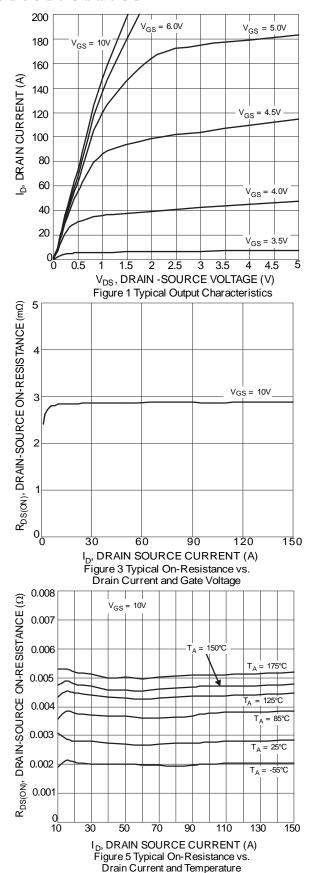
^{7.} Short duration pulse test used to minimize self-heating effect.

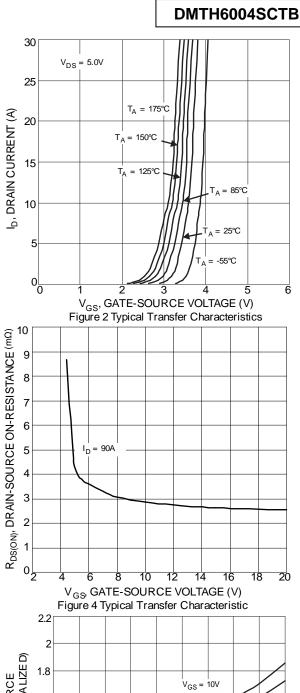
^{8.} Guaranteed by design. Not subject to product testing.

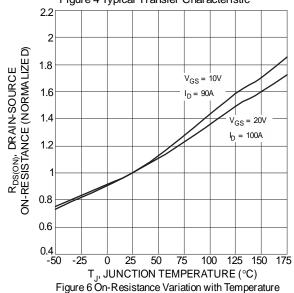
^{9.} Package limited.





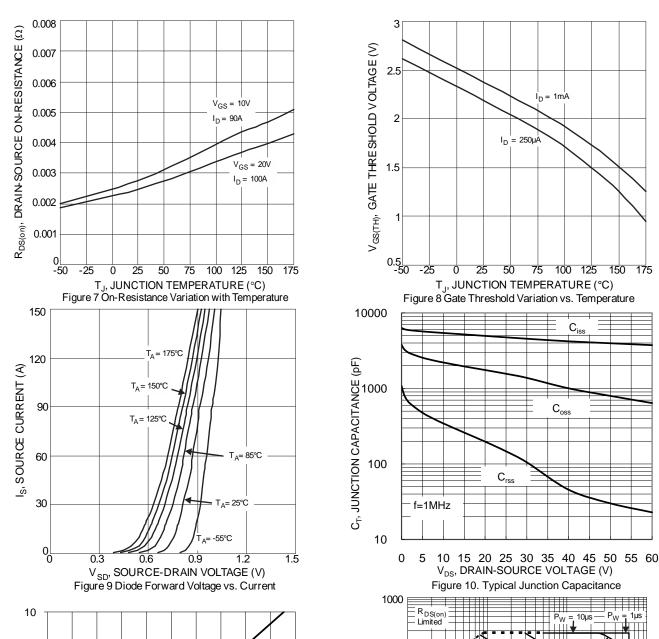


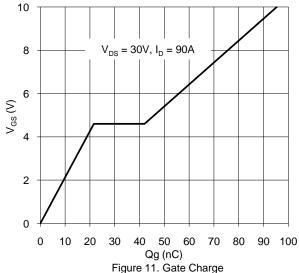




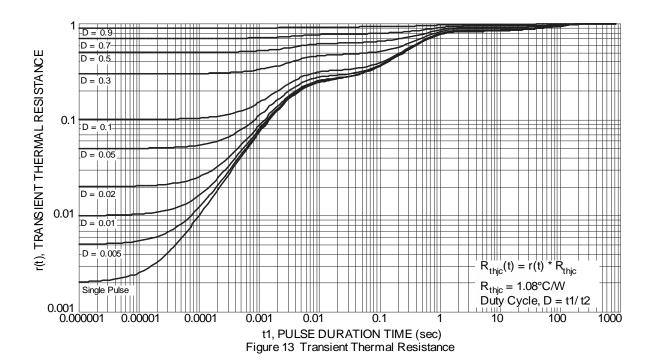
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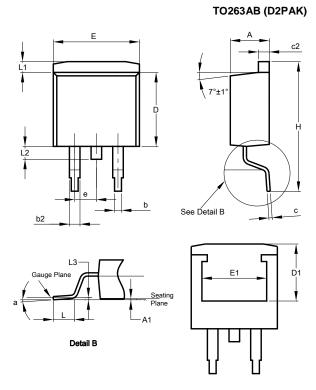






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

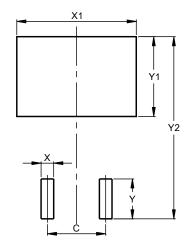


TO263AB (D2PAK)					
Dim	Min	Max	Тур		
Α	4.07	4.82	_		
A1	0.00	0.25	_		
b	0.51	0.99	_		
b2	1.15	1.77	_		
С	0.356	0.73	_		
c2	1.143	1.65	_		
D	8.39	9.65	_		
D1	6.55	6.95	_		
е		2.54 T\	/P		
Е	9.66	10.66	_		
E1	6.23	8.23	_		
Н	14.61	15.87	_		
L	1.78	2.79	_		
L1	_	1.67	_		
L2	_	1.77	_		
L3	_	_	0.254		
а	0°	8°	_		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

TO263AB (D2PAK)



Dimensions	Value (in mm)		
С	5.08		
Х	1.10		
X1	10.41		
Υ	3.50		
Y1	7.01		
Y2	15 99		



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